

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of : Customer Number: 20277
: Confirmation Number:
Masahiro NAKAYAMA, et al. :
Serial No.: Group Art Unit:
: Examiner: Unknown
Filed: September 22, 2003 :
: For: NITRIDE SEMICONDUCTOR WAFER AND METHOD OF PROCESSING NITRIDE
SEMICONDUCTOR WAFER

INFORMATION DISCLOSURE STATEMENT

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Commissioner for Patents
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Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

The relevance of the references listed on attached Form 1449 is discussed in the present specification.

Serial No.:

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)			ATTY. DOCKET NO. 52775-025	SERIAL NO.		
			APPLICANT Masahiro NAKAYAMA, et al.			
			FILING DATE September 22, 2003	GROUP		
U.S. PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ₂ (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
	US					
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FOREIGN PATENT DOCUMENTS						
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number & Kind Codes (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation
		WO99/23693	05/14/1999	SUMITOMO ELECTRIC IND LTD		Yes No
		JP P2000-22212A	01/21/2000	SUMITOMO ELECTRIC IND LTD		(Japan w/English Abstract)
		JP P2000-12900A	01/14/2000	SUMITOMO ELECTRIC IND LTD		(Japan w/English Abstract)
		JP P2001-102307A	04/13/2001	SUMITOMO ELECTRIC IND LTD		(Japan w/English Abstract)
		JP P2003-165799A	06/10/2003	SUMITOMO ELECTRIC IND LTD		(Japan w/English Abstract)
		JP 10-166259	06/23/1998	OKAMOTO KOSAKU KIKAI SEISAKUSHO:KK		(Japan w/English Abstract)
		JP P2002-356398A	12/13/2002	SUMITOMO ELECTRIC IND LTD		(Japan w/English Abstract)
		JP P2002-261014A	09/13/2002	NICHIA CHEM IND LTD		(Japan w/English Abstract)
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)						
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				
		"Thick Layer Growth of GaN by Hydride Vapor Phase Epitaxy", IEICE, C-II, vol. J81-C-II, No.1, pp58-64 (1998)				
		"Preparation of Large Freestanding GaN Substrates by Hydride Vapor Phase Epitaxy Using GaAs as a Starting Substrate", Jpn. J. Appl. Phys. Vol. 40 (2001) pp.L140-143				
		"Chemical polishing of bulk and epitaxial GaN", Journal of Crystal Growth 182(1997), p17-22				
		"Ultraviolet photoenhanced wet etching of GaN in K ₂ S ₂ O ₈ solution", J. Appl. Phys., Vol.89, No.7, 1 April 2001.				
EXAMINER			DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.